

# International IOR Rectifier

- Logic-Level Gate Drive
- Advanced Process Technology
- Surface Mount (IRL3303S)
- Low-profile through-hole (IRL3303L)
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Lead-Free

## Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D<sup>2</sup>Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D<sup>2</sup>Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.

The through-hole version (IRL3303L) is available for low-profile applications.

## Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}^{\text{⑤}}$	38	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}^{\text{⑤}}$	27	
$I_{DM}$	Pulsed Drain Current $\text{①}^{\text{⑤}}$	140	
$P_D @ T_A = 25^\circ\text{C}$	Power Dissipation	3.8	W
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	68	W
	Linear Derating Factor	0.45	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 16$	V
$E_{AS}$	Single Pulse Avalanche Energy $\text{②}^{\text{⑤}}$	130	mJ
$I_{AR}$	Avalanche Current $\text{①}$	20	A
$E_{AR}$	Repetitive Avalanche Energy $\text{①}$	6.8	mJ
dv/dt	Peak Diode Recovery dv/dt $\text{③}^{\text{⑤}}$	5.0	V/ns
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	

## Thermal Resistance

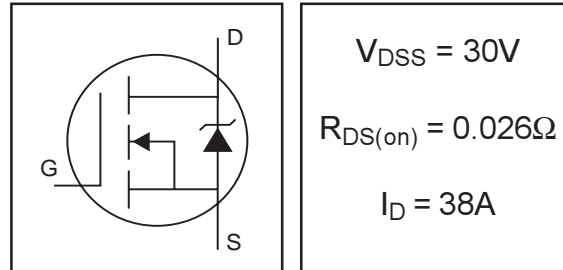
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	---	2.2	°C/W
$R_{\theta JA}$	Junction-to-Ambient ( PCB Mounted, steady-state)**	---	40	

PD - 95578

IRL3303LPbF

IRL3303SPbF

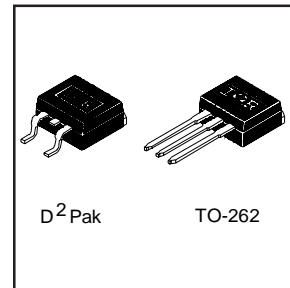
HEXFET® Power MOSFET



$$V_{DSS} = 30\text{V}$$

$$R_{DS(on)} = 0.026\Omega$$

$$I_D = 38\text{A}$$



D<sup>2</sup>Pak

TO-262

## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.035	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA <sup>③</sup>
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	0.026	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A <sup>④</sup>
		—	—	0.040		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 17A <sup>④</sup> T <sub>J</sub> = 150°C
V <sub>GS(th)</sub>	Gate Threshold Voltage	1.0	—	—	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
g <sub>fs</sub>	Forward Transconductance	12	—	—	S	V <sub>DS</sub> = 25V, I <sub>D</sub> = 20A <sup>④</sup>
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	25	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 150°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 16V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -16V
Q <sub>g</sub>	Total Gate Charge	—	—	26	nC	I <sub>D</sub> = 20A
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	8.8		V <sub>DS</sub> = 24V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	—	15		V <sub>GS</sub> = 4.5V, See Fig. 6 and 13 <sup>④⑤</sup>
t <sub>d(on)</sub>	Turn-On Delay Time	—	7.4	—		V <sub>DD</sub> = 15V
t <sub>r</sub>	Rise Time	—	200	—		I <sub>D</sub> = 20A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	14	—		R <sub>G</sub> = 6.5Ω
t <sub>f</sub>	Fall Time	—	36	—		R <sub>D</sub> = 0.7Ω, See Fig. 10 <sup>④⑤</sup>
L <sub>S</sub>	Internal Source Inductance	—	7.5	—	nH	Between lead, and center of die contact
C <sub>iss</sub>	Input Capacitance	—	870	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	340	—		V <sub>DS</sub> = 25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	170	—		f = 1.0MHz, See Fig. 5 <sup>⑤</sup>

## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	38	A	MOSFET symbol showing the integral reverse p-n junction diode.
I <sub>SM</sub>	Pulsed Source Current (Body Diode) <sup>①</sup>	—	—	140		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 20A, V <sub>GS</sub> = 0V <sup>④</sup>
t <sub>rr</sub>	Reverse Recovery Time	—	72	110	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 20A
Q <sub>rr</sub>	Reverse Recovery Charge	—	180	280	nC	di/dt = 100A/μs <sup>④⑤</sup>
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )
- ② V<sub>DD</sub> = 15V, starting T<sub>J</sub> = 25°C, L = 470μH  
R<sub>G</sub> = 25Ω, I<sub>AS</sub> = 20A. (See Figure 12)
- ③ I<sub>SD</sub> ≤ 20A, di/dt ≤ 140A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>,  
T<sub>J</sub> ≤ 175°C
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ Uses IRL3303 data and test conditions.

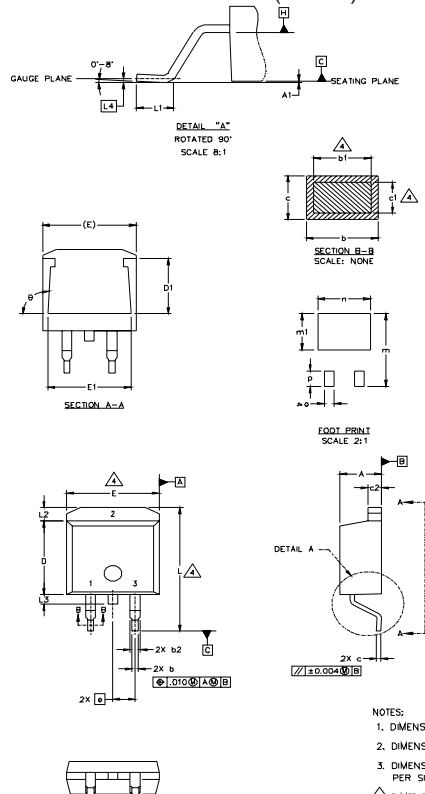
\*\* When mounted on 1" square PCB ( FR-4 or G-10 Material ).  
For recommended footprint and soldering techniques refer to application note #AN-994.

# IRL3303S/LPbF

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## D<sup>2</sup>Pak Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	4
A1		0.127		.005	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	4
c	0.43	0.63	.017	.025	
c1	0.38	0.74	.015	.029	
c2	1.14	1.40	.045	.055	3
D	8.51	9.65	.335	.380	
D1	5.33		.210		3
E	9.65	10.67	.380	.420	
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	14.61	15.88	.575	.625	
L1	1.78	2.79	.070	.110	
L2			1.65	.065	
L3	1.27	1.78	.050	.070	
L4	0.25 BSC		.010 BSC		
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
θ	90°	93°	90°	93°	

### LEAD ASSIGNMENTS

HEXFET	IGBTs, CoPACK	DIODES
1.- GATE	1.- GATE	1.- ANODE *
2.- DRAIN	2.- COLLECTOR	2.- CATHODE
3.- SOURCE	3.- EMITTER	3.- ANODE

\* PART DEPENDENT

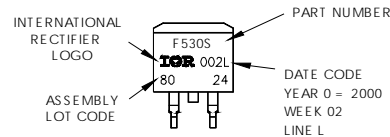
### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
- DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
- CONTROLLING DIMENSION: INCH.

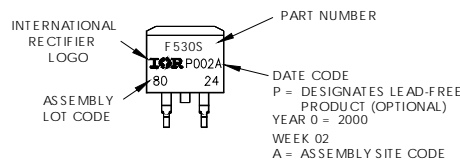
## D<sup>2</sup>Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH  
LOT CODE 8024  
ASSEMBLED ON WW 02, 2000  
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line  
position indicates "Lead-Free"



**OR**

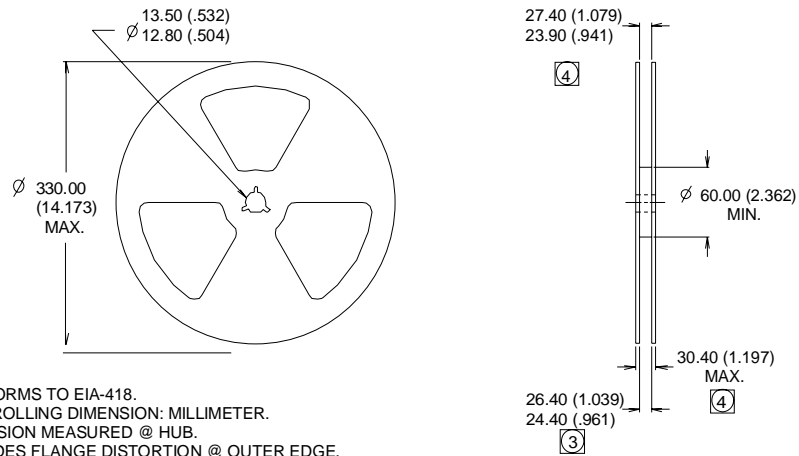
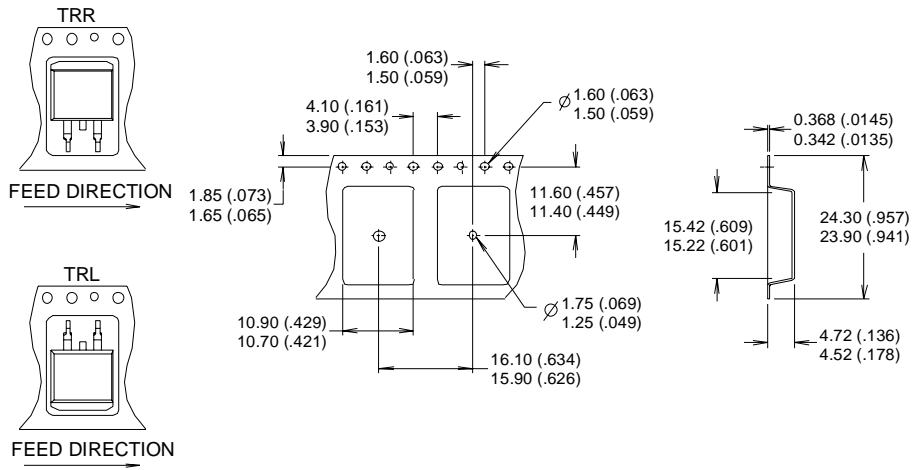


# IRL3303S/LPbF

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## D<sup>2</sup>Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



Data and specifications subject to change without notice.

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